

VERTICAL DEFLECTION BOOSTER

ADVANCE DATA

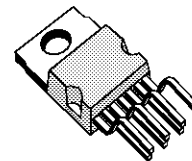
- POWER AMPLIFIER
- THERMAL PROTECTION
- OUTPUT CURRENT UP TO 2.0A_{PP}
- FLYBACK VOLTAGE UP TO 90V (on Pin 5)
- INTERNAL REFERENCE VOLTAGE
- EXTERNAL FLYBACK SUPPLY

DESCRIPTION

Designed for monitors and high performance TVs, the STV9378F vertical deflection booster can handle flyback voltage up to 90V. More than this it is possible to have a flyback voltage which is more than the double of the supply (Pin 2). This allows to decrease the power consumption or to decrease the flyback time for a given supply voltage.

The STV9378F operates with supplies up to 42V and provides up to 2A_{pp} output current to drive the yoke.

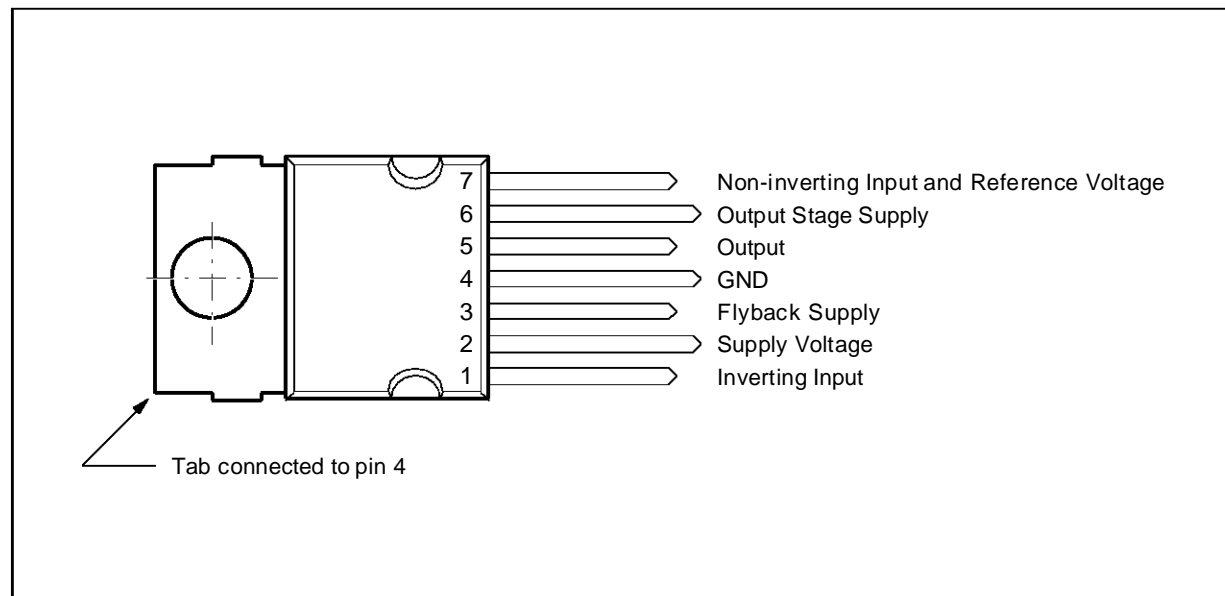
The STV9378F is offered in HEPTAWATT package.



HEPTAWATT
(Plastic Package)

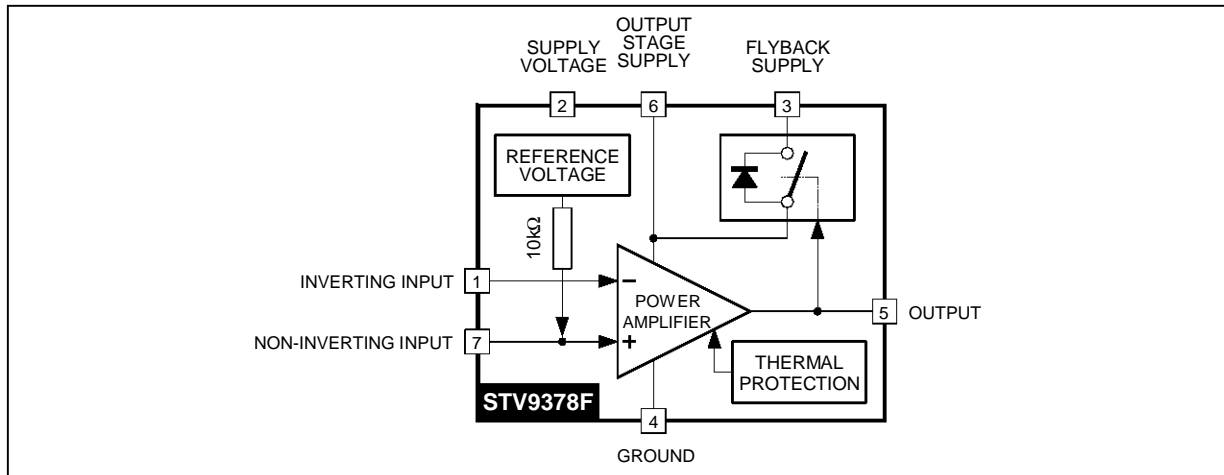
ORDER CODE : STV9378F

PIN CONNECTIONS



9378F-01.EPS

BLOCK DIAGRAM



9378F-02.EPS

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _S	Supply Voltage (Pin 2) (see note 1)	50	V
V ₆	Flyback Peak Voltage (Pin 6) (see note 1)	100	V
V ₁ , V ₇	Amplifier Input Voltage (Pins 1-7) (see note 1)	- 0.3, + V _S	V
I _O	Maximum Output Peak Current (see notes 2 and 3)	1.5	A
I ₃	Maximum Sink Current (t < 1ms)	1.5	A
I ₃	Maximum Source Current (t < 1ms) (in the diode, see Block Diagram)	1.5	A
V ₃ - V ₂	Voltage Difference between Flyback Supply and Supply Voltage	70	V
T _{oper}	Operating Ambient Temperature	- 20, + 75	°C
T _{stg}	Storage Temperature	- 40, + 150	°C
T _j	Junction Temperature	+150	°C

9378F-01.TBL

- Notes :**
1. Versus GND.
 2. The output current can reach 4A peak for t ≤ 10μs (up to 120Hz).
 3. Provided SOAR is respected (see Figures 1 and 2).

THERMAL DATA

Symbol	Parameter	Value	Unit
R _{th(j-c)}	Junction-case Thermal Resistance	Max. 3	°C/W
T _t	Temperature for Thermal Shutdown	150	°C
ΔT _t	Hysteresis on T _t	10	°C
T _{jr}	Recommended Max. Junction Temperature	120	°C

9378F-02.TBL

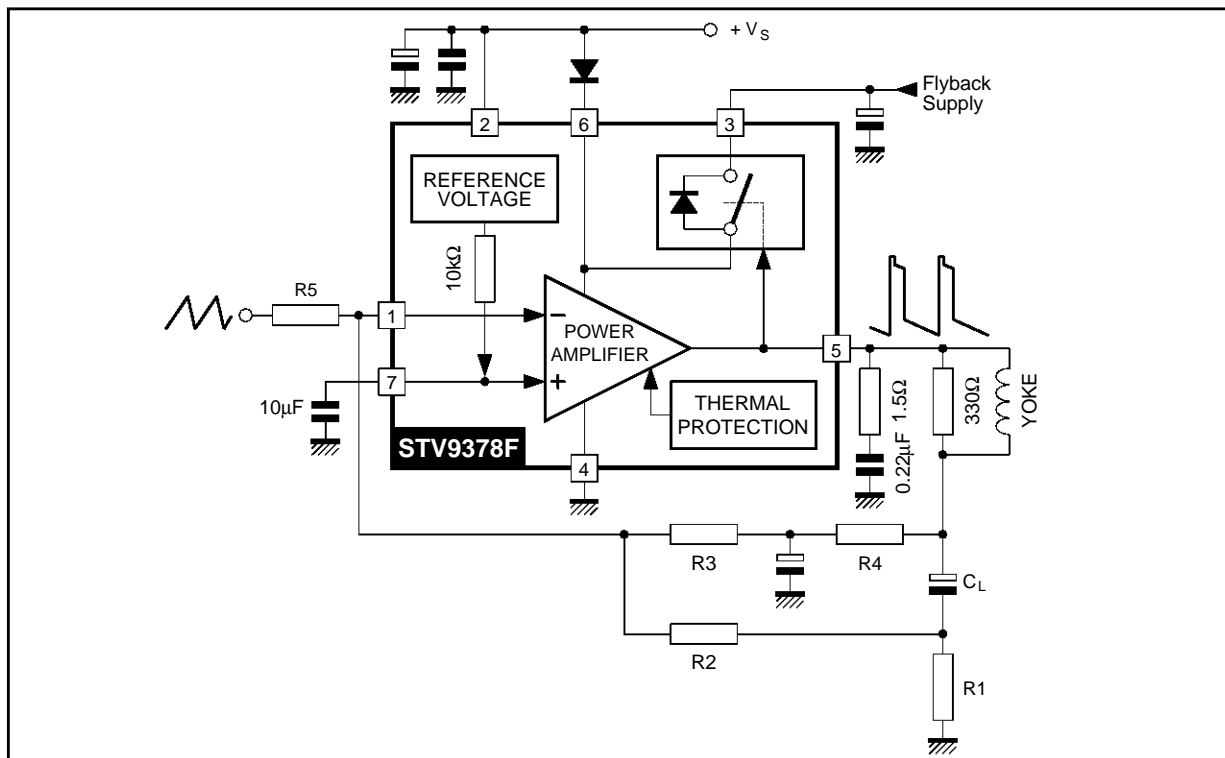
ELECTRICAL CHARACTERISTICS

($V_S = 42V$, $T_A = 25^\circ C$, unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V_S	Operating Supply Voltage Range		10		42	V
V_{3M}	Operating Flyback Supply Voltage		V_S		90	V
I_2	Pin 2 Quiescent Current	$I_3 = 0, I_5 = 0$		10	20	mA
I_6	Pin 6 Quiescent Current	$I_3 = 0, I_5 = 0$	5	10	30	mA
I_O	Max. Peak Output Current				1	A
I_1	Amplifier Bias Current	$V_1 = 1V$		- 0.15	- 1	μA
V_7	Internal Reference Voltage		2.2	2.3	2.4	V
$\frac{\Delta V_7}{\Delta V_S}$	Reference Voltage Drift versus V_S	$V_S = 24$ to $42V$		2	4	mV/V
Kt	Reference Voltage Drift versus T_j			100	150	ppm/ $^\circ C$
GV	Voltage Gain		80			dB
V_{5L}	Output Saturation Voltage to GND (Pin 4)	$I_5 = 1A$		1	1.5	V
V_{5H}	Output Saturation Voltage to Supply (Pin 6)	$I_5 = - 1A$		1.6	2.1	V
V_{D5-6}	Diode Forward Voltage between Pins 5-6	$I_5 = 1A$		1.5	2	V
V_{D3-6}	Diode Forward Voltage between Pins 3-6	$I_3 = 1A$		1.5	2	V
V_{3-6}	Voltage Drop between Pins 3-6 (2nd part of flyback)	$I_3 = - 1A$		2.1	2.9	V

9378F-03.TEL

APPLICATION CIRCUIT



9378F-03.EPS

Figure 1 : Output Transistors SOA
(for secondary breakdown)

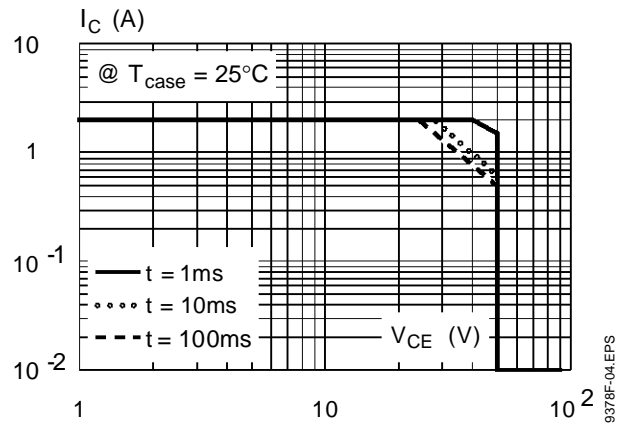
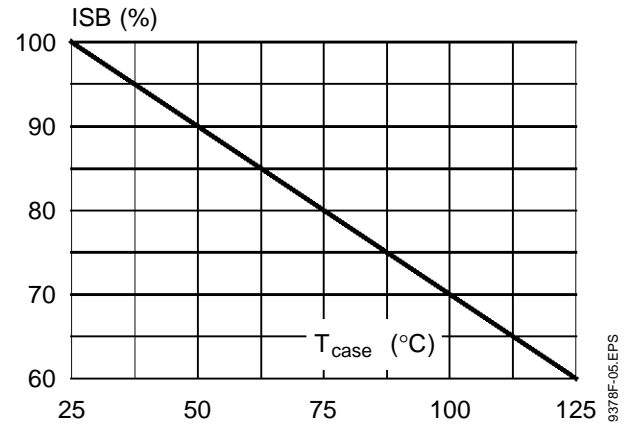
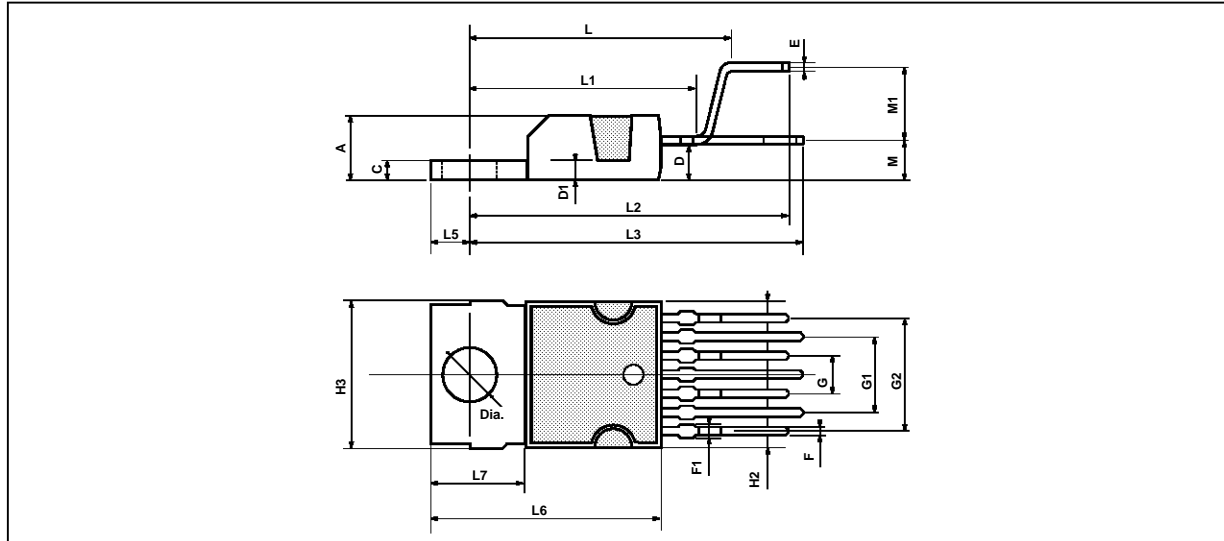


Figure 2 : Secondary Breakdown Temperature Derating Curve
(ISB = secondary breakdown current)



PACKAGE MECHANICAL DATA : 7 PINS - PLASTIC HEPTAWAT



PM-HEPTV.EPS

Dimensions	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A			4.8			0.189
C			1.37			0.054
D	2.4		2.8	0.094		0.110
D1	1.2		1.35	0.047		0.053
E	0.35		0.55	0.014		0.022
F	0.6		08	0.024		0.031
F1			0.9			0.035
G	2.41	2.54	2.67	0.095	0.100	0.105
G1	4.91	5.08	5.21	0.193	0.200	0.205
G2	7.49	7.62	7.8	0.295	0.300	0.307
H2			10.4			0.409
H3	10.05		10.4	0.396		0.409
L		16.97			0.668	
L1		14.92			0.587	
L2		21.54			0.848	
L3		22.62			0.891	
L5	2.6		3	0.102		0.118
L6	15.1		15.8	0.594		0.622
L7	6		6.6	0.236		0.260
M		2.8			0.110	
M1		5.08			0.200	
Dia.	3.65		3.85	0.144		0.152

HEPTV.TBL

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